Complementary Silicon Plastic Power Transistors

MJE15028, MJE15030 (NPN), MJE15029, MJE15031 (PNP)

These devices are designed for use as high−frequency drivers in audio amplifiers.

Features

- High Current Gain − Bandwidth Product
- TO−220 Compact Package
- These Devices are Pb−Free and are RoHS Compliant*

1 2 3

MARKING DIAGRAM

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector−Emitter Voltage MJE15028G, MJE15029G MJE15030G, MJE15031G	V_{CEO}	 120 150	Vdc
Collector−Base Voltage MJE15028G, MJE15029G MJE15030G, MJE15031G	V_{CB}	 120 150	Vdc
Emitter−Base Voltage	V_{EB}	5.0	Vdc
Collector Current − Continuous	I_C	8.0	Adc
Collector Current − Peak	I_{CM}	16	Adc
Base Current	I_B	2.0	Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	 50 0.40	 W W/°C
Total Device Dissipation @ T_A = 25°C Derate above 25°C			

	$R_{\theta JC}$	2.5

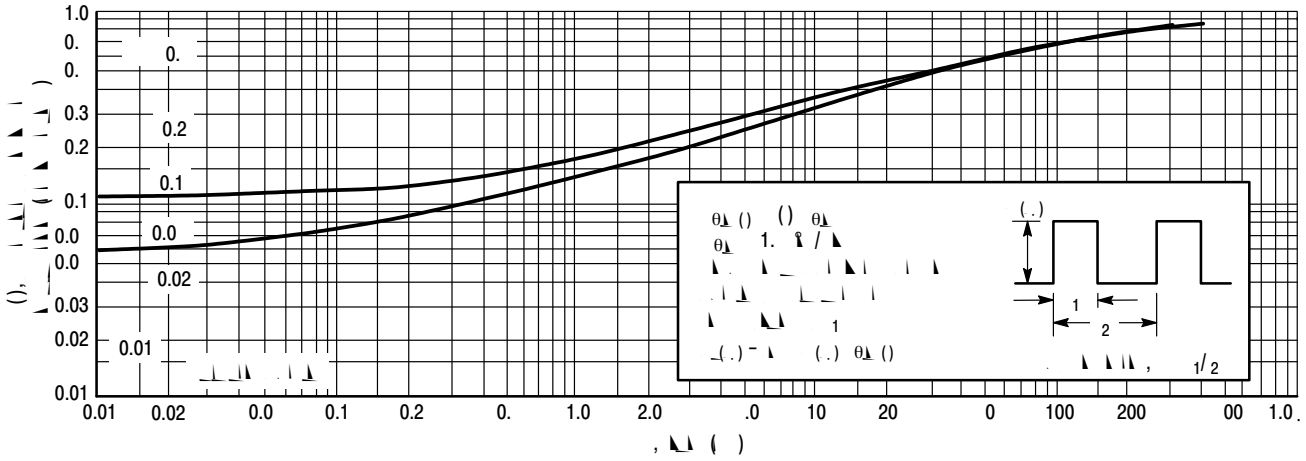


Figure 2. Thermal Response

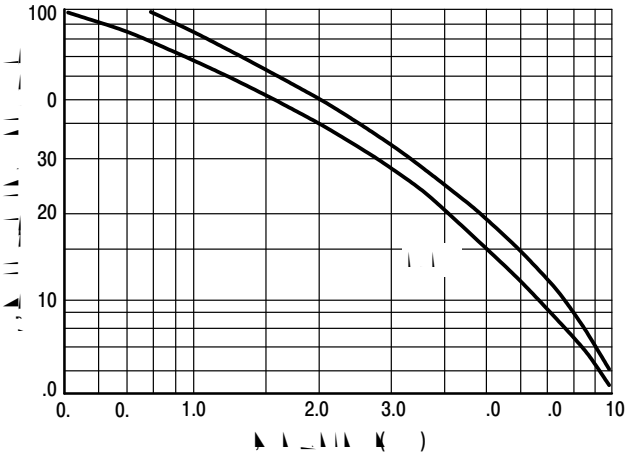


Figure 6. Small−Signal Current Gain

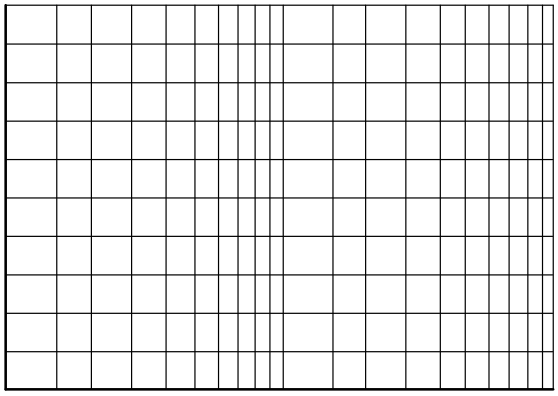
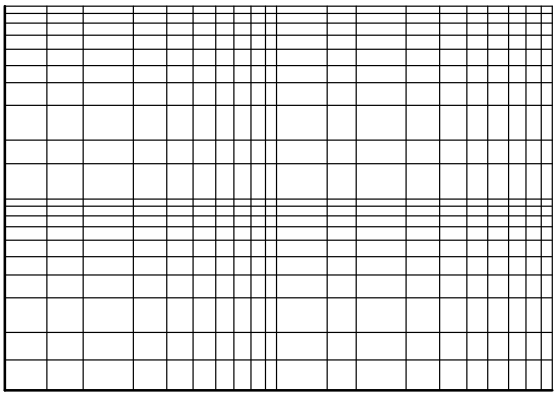


Figure 7. Current Gain−, SMALL SIGN3200ORfBT8 00 AM90.06



TO−220−3 10.10x15.12x4.45, 2.54P
CASE 221A
ISSUE AL

DATE 05 FEB 2025

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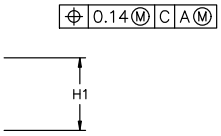

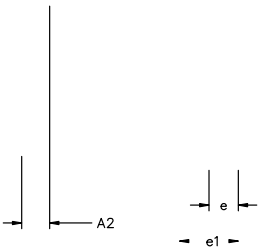

0.15 M C A M

MILLIMETERS			
DIM	MIN	NOM	MAX
A	4.07	4.45	4.83
A1	1.15	1.28	1.41
A2	2.04	2.42	2.79
b	1.15	1.34	1.52
b1	0.64	0.80	0.96
c	0.36	0.49	0.61
D	9.66	10.10	10.53
D1	8.43	8.63	8.83
E	14.48	15.12	15.75
E1	12.58	12.78	12.98
E2	1.27 REF		

MILLIMETERS			
DIM	MIN	NOM	MAX
e	2.42	2.5	
			J
Q	2.54	2.79	3.04
øP	3.60	3.85	4.09
Z	−.−−	−.−−	3.48

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.

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